

The Crystal and Molecular Structure of 1,2-Bis-(diphenylphosphino)ethane-bis(trimethylgallium)

ALAN BOARDMAN, RONALD W. H. SMALL and IAN J. WORRALL

Department of Chemistry, The University of Lancaster, Lancaster, U.K.

(Received May 28, 1986)

The ligand 1,2-bis(diphenylphosphino)ethane (diphos) forms weak complexes with several group III metal alkyls; the complexes readily undergo thermal dissociation and since the ligand has low volatility at the adduct's dissociation temperature, the dissociative process effects a means of purification of the Lewis acids. The volatile metal alkyls $(\text{CH}_3)_3\text{M}$ ($\text{M} = \text{Ga}, \text{In}$) which are used in synthesizing III–V compounds may be purified by this method [1]. We here report the crystal structure of the gallium compound.

Experimental

The adduct was prepared by mixing benzene solutions of trimethylgallium and diphos *in vacuo*. Solvent was then removed to concentrate the solution and colourless crystals, suitable for X-ray analysis, were deposited. The structure of $(\text{C}_6\text{H}_5)_2\text{PCH}_2\text{CH}_2\text{P}(\text{C}_6\text{H}_5)_2\{\text{Ga}(\text{CH}_3)_3\}_2$ was solved by a single crystal X-ray study.

Crystal Data (20 °C)

Triclinic, space group $P\bar{1}$, $a = 8.970(5)$, $b = 11.94(1)$, $c = 9.935(5)$ Å, $\alpha = 118.3(1)$, $\beta = 65.8(1)$, $\gamma = 103.2(1)^\circ$, $\mu = 1.62 \text{ mm}^{-1}$. Intensity measurements were made on a Stoe STADI-2 diffractometer using $\text{Mo K}\alpha$ radiation. 3299 reflections were measured, and after elimination of those for which $I < 3\sigma(I)$ there remained 2220 unique reflections which were used in the final refinement. The structure was solved using the SHELX suite of programs [2]. Ga atom positions, obtained from Patterson maps, were used to phase ($F_o - F_c$) maps to give the positions of the remaining atoms (except hydrogen). Full matrix least-squares refinement of all atomic positions, anisotropic U_{ij} for Ga and P, and isotropic U values for C were carried out until convergence was reached at $R = 0.078$. Fractional atomic coordinates are given in Table I. See also 'Supplementary Material'.

Results and Discussion

The X-ray crystallographic study revealed the presence of discrete molecules in the solid state (Fig. 1).

TABLE I. Fractional Atomic Coordinates ($\times 10^4$)

Atom	x	y	z
C(1)	5011(13)	2041(10)	4104(13)
C(2)	3902(16)	1459(12)	5139(16)
C(3)	4186(18)	1558(14)	6542(18)
C(4)	5582(18)	2246(14)	6870(18)
C(5)	6662(18)	2860(14)	5878(18)
C(6)	6375(15)	2743(12)	4473(16)
C(7)	5511(15)	3992(12)	1691(15)
C(8)	6004(12)	2807(9)	1336(12)
C(9)	7562(14)	2399(11)	233(15)
C(10)	8638(16)	3163(13)	-586(17)
C(11)	8131(16)	4338(12)	-249(16)
C(12)	6596(17)	4744(13)	888(17)
C(13)	5108(13)	191(10)	838(13)
C(14)	1537(21)	2593(17)	1195(24)
C(15)	289(21)	705(16)	3405(21)
C(16)	1391(19)	3913(15)	5318(19)
Ga	1545(2)	2321(1)	3161(2)
P	4522(3)	1834(3)	2306(3)

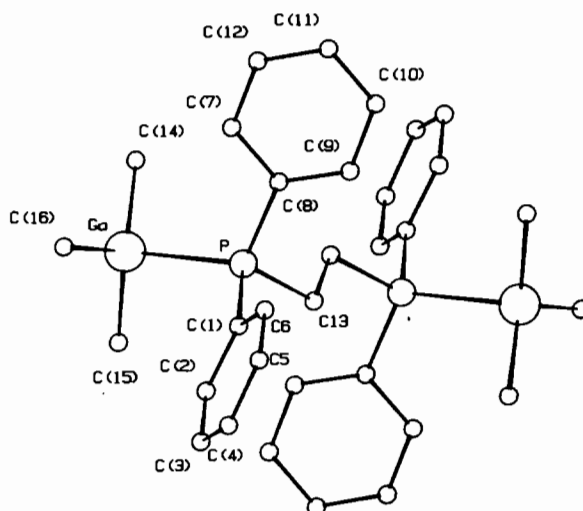


Fig. 1. The molecular structure of 1,2-bis(diphenylphosphino)ethane-bis(trimethylgallium).

The complex has a centre of symmetry imposed crystallographically and there are no short intermolecular contacts. Selected bond distances and angles are given in Table II. The weak interaction between $\text{Ga}(\text{CH}_3)_3$ and the Lewis base is reflected in the long Ga–P bond and the large C–Ga–C bond angles (average 116.3°). The Ga–P distance ($2.563(3)$ Å) greatly exceeds that observed in $(\text{CH}_3)_3\text{P}-\text{GaCl}_3$ ($2.353(2)$ Å) [3] which is close to the sum of the single-bond covalent radii for Ga and P (2.30 Å). The Ga–P bond is slightly longer than observed in the analogous bis(diphenylphosphino)methane-chlorodimethylgallium ($2.535(2)$ Å) [4].

TABLE II. Selected Bond Distances (Å) and Angles (°) in $\text{Diphos} \cdot 2\text{Ga}(\text{CH}_3)_3$

Distances			
Ga-P	2.563(3)	Ga-C(14)	2.13(2)
Ga-C(15)	2.07(2)	Ga-C(16)	2.06(2)
P-C(1)	1.90(1)	P-C(8)	1.83(1)
P-C(13)	1.84(1)	C(13)-C(13')	1.58(2)
Angles			
P-Ga-C(16)	97.9(4)	C(14)-Ga-C(16)	117.4(7)
P-Ga-C(15)	102.2(5)	C(14)-Ga-C(15)	116.1(7)
P-Ga-C(14)	103.7(5)	C(15)-Ga-C(16)	115.3(7)
C(8)-P-C(1)	108.6(5)	C(13)-P-C(1)	102.1(5)
C(13)-P-C(8)	104.0(5)	Ga-P-C(1)	111.8(3)
Ga-P-C(8)	113.2(3)	Ga-P-C(13)	116.2(4)

Supplementary Material

Lists of structure factors and thermal parameters are available on request from the authors.

References

- 1 D. C. Bradley, M. M. Faktor and S. J. Watts, *International Symposium on Uses of Metal Organic Compounds*, Oxford, 1985.
- 2 G. M. Sheldrick, 'SHELX 76', program for crystal structure determination, University of Cambridge, U.K., 1976.
- 3 J. C. Carter, G. Jugie, R. Enjalbert and J. Galy, *Inorg. Chem.*, *17*, 1248 (1978).
- 4 H. Schmidbaur, S. Lauteschlager and G. Muller, *J. Organomet. Chem.*, *281*, 25 (1985).